

# PSMN8R7-80PS

# N-channel 80 V 8.7 m $\Omega$ standard level MOSFET in TO-220 Rev. 02 — 1 November 2010 Product data

**Product data sheet** 

### **Product profile** 1.

# 1.1 General description

Standard level N-channel MOSFET in TO-220 package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

### 1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive

# 1.3 Applications

- DC-to-DC converters
- Load switching

- Motor control
- Server power supplies

### 1.4 Quick reference data

Table 1. Quick reference data

| Symbol               | Parameter  | Conditions  |     | Min | Тур | Max | Unit |
|----------------------|--|---|-----|-----|-----|-----|------|
| $V_{DS}$             | drain-source voltage                               | $T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}$   |     | -   | -   | 80  | V    |
| I <sub>D</sub>       | drain current                                      | $T_{mb}$ = 25 °C; $V_{GS}$ = 10 V;<br>see <u>Figure 1</u>   |     | -   | -   | 90  | Α    |
| P <sub>tot</sub>     | total power dissipation                            | T <sub>mb</sub> = 25 °C; see Figure 2   |     | -   | -   | 170 | W    |
| Tj                   | junction temperature                               |   |     | -55 | -   | 175 | °C   |
| Static chara         | acteristics  |   |     |     |     |     |      |
| DOON                 | drain-source on-state resistance                   | $V_{GS} = 10 \text{ V}; I_D = 10 \text{ A};$<br>$T_j = 100 \text{ °C}; \text{ see } \frac{\text{Figure 12}}{\text{ or } 100 \text{ or } $ |     | -   | -   | 14  | mΩ   |
|                      |  | $V_{GS} = 10 \text{ V}; I_D = 10 \text{ A};$<br>$T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 13}{\text{ Constant } 13}$  | [1] | -   | 7.5 | 8.7 | mΩ   |
| Dynamic ch           | naracteristics                                     |   |     |     |     |     |      |
| $Q_{GD}$             | gate-drain charge                                  | $V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$  |     | -   | 11  | -   | nC   |
| Q <sub>G(tot)</sub>  | total gate charge                                  | $V_{DS} = 40 \text{ V}$ ; see <u>Figure 14</u> ; see <u>Figure 15</u>   |     | -   | 52  | -   | nC   |
| Avalanche            | ruggedness   |   |     |     |     |     |      |
| E <sub>DS(AL)S</sub> | non-repetitive<br>drain-source avalanche<br>energy | $\begin{split} &V_{GS} = 10 \text{ V; } T_{j(\text{init})} = 25 \text{ °C;} \\ &I_D = 90 \text{ A; } V_{\text{sup}} \leq 80 \text{ V;} \\ &R_{GS} = 50  \Omega; \text{ unclamped} \end{split}$  |     | -   | -   | 120 | mJ   |

<sup>[1]</sup> Measured 3 mm from package.



# 2. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description                       | Simplified outline | Graphic symbol    |
|-----|--------|-----------------------------------|--------------------|-------------------|
| 1   | G      | gate                              |                    |                   |
| 2   | D      | drain                             | mb                 | D                 |
| 3   | S      | source                            |                    | <sub>G</sub> (EA) |
| mb  | D      | mounting base; connected to drain | 1 2 3              | mbb076 S          |
|     |        |                                   | SOT78 (TO-220AB)   |                   |

# 3. Ordering information

Table 3. Ordering information

| Type number  | Package  |  |         |
|--------------|----------|--|---------|
|              | Name     | Description  | Version |
| PSMN8R7-80PS | TO-220AB | plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB | SOT78   |

# 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

|                      |  | - , , ,  |     |     |      |
|----------------------|--|--|-----|-----|------|
| Symbol               | Parameter                                    | Conditions   | Min | Max | Unit |
| $V_{DS}$             | drain-source voltage                         | T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C  | -   | 80  | V    |
| $V_{DGR}$            | drain-gate voltage                           | $T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$                               | -   | 80  | V    |
| $V_{GS}$             | gate-source voltage                          |  | -20 | 20  | V    |
| I <sub>D</sub>       | drain current                                | V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C; see <u>Figure 1</u>                                      | -   | 64  | Α    |
|                      |  | $V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{\text{M}}$             | -   | 90  | Α    |
| I <sub>DM</sub>      | peak drain current                           | pulsed; $t_p \le 10 \mu s$ ; $T_{mb} = 25  ^{\circ}C$ ; see <u>Figure 3</u>                                | -   | 361 | Α    |
| P <sub>tot</sub>     | total power dissipation                      | T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>   | -   | 170 | W    |
| T <sub>stg</sub>     | storage temperature                          |  | -55 | 175 | °C   |
| Tj                   | junction temperature                         |  | -55 | 175 | °C   |
| T <sub>sld(M)</sub>  | peak soldering temperature                   |  | -   | 260 | °C   |
| Source-drai          | n diode                                      |  |     |     |      |
| Is                   | source current                               | T <sub>mb</sub> = 25 °C  | -   | 90  | Α    |
| I <sub>SM</sub>      | peak source current                          | pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$   | -   | 361 | Α    |
| Avalanche r          | uggedness                                    |  |     |     |      |
| E <sub>DS(AL)S</sub> | non-repetitive drain-source avalanche energy | $V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 90 A; $V_{sup}$ ≤ 80 V; $R_{GS}$ = 50 $\Omega$ ; unclamped | -   | 120 | mJ   |
|                      |  |  |     |     |      |

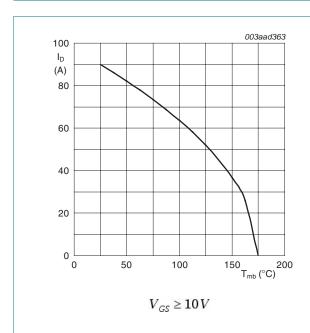


Fig 1. Continuous drain current as a function of mounting base temperature

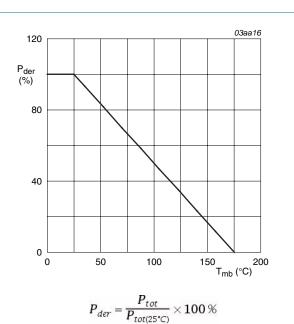


Fig 2. Normalized total power dissipation as a function of mounting base temperature

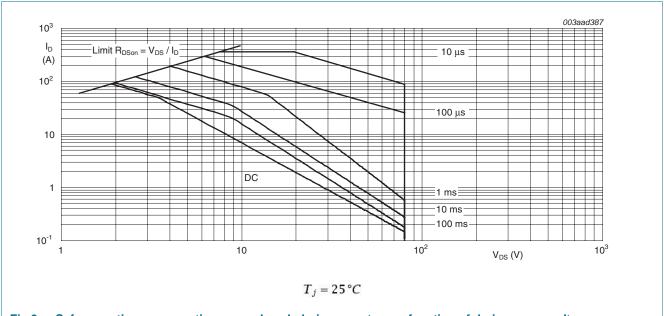


Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

# 5. Thermal characteristics

Table 5. Thermal characteristics

| Symbol         | Parameter   | Conditions   | Min | Тур  | Max  | Unit |
|----------------|---|--------------|-----|------|------|------|
| $R_{th(j-mb)}$ | thermal resistance from junction to mounting base | see Figure 4 | -   | 0.54 | 0.88 | K/W  |

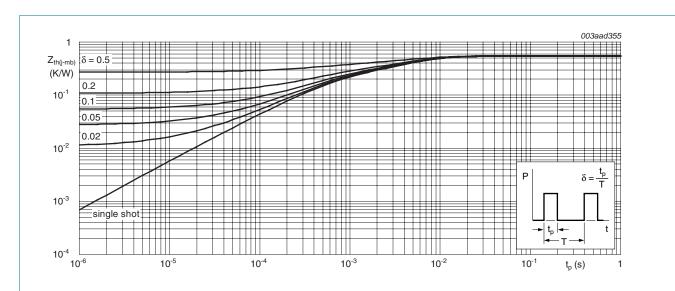


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration; typical values

# 6. Characteristics

Table 6. Characteristics

Tested to JEDEC standards where applicable.

| Symbol                            | Parameter                         | Conditions  | Min   | Тур  | Max       | Uni |
|-----------------------------------|-----------------------------------|---|-------|------|-----------|-----|
| Static cha                        | racteristics                      |   |       |      |           |     |
| V <sub>(BR)DSS</sub>              | drain-source breakdown voltage    | $I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 ^{\circ}C$  | 73    | -    | -         | V   |
|                                   |                                   | $I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$  | 80    | -    | -         | V   |
| $V_{GS(th)}$                      | gate-source threshold voltage     | $I_D = 1 \text{ mA}$ ; $V_{DS} = V_{GS}$ ; $T_j = 175 \text{ °C}$ ; see Figure 10                   | 1     | -    | -         | V   |
|                                   |                                   | $I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = -55$ °C; see Figure 10                                     | -     | -    | 4.6       | V   |
|                                   |                                   | $I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = 25$ °C;<br>see <u>Figure 11</u> ; see <u>Figure 10</u>     | 2.3   | 3    | 4         | V   |
| I <sub>DSS</sub> drain leakage cu | drain leakage current             | $V_{DS} = 80 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$                                  | -     | 0.3  | 5         | μΑ  |
|                                   |                                   | V <sub>DS</sub> = 80 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 125 °C                              | -     | -    | 100       | μΑ  |
| I <sub>GSS</sub>                  | gate leakage current              | $V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$                                 | -     | 10   | 100       | nΑ  |
|                                   |                                   | $V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$                                  | -     | 10   | 100       | nA  |
| R <sub>DSon</sub> drai            | drain-source on-state resistance  | $V_{GS} = 10 \text{ V}; I_D = 10 \text{ A}; T_j = 175 °C;$<br>see <u>Figure 12</u>                  | -     | -    | 20.8<br>8 | mΩ  |
|                                   |                                   | $V_{GS} = 10 \text{ V}; I_D = 10 \text{ A}; T_j = 100 \text{ °C};$<br>see Figure 12                 | -     | -    | 14        | mΩ  |
|                                   |                                   | $V_{GS} = 10 \text{ V}; I_D = 10 \text{ A}; T_j = 25 \text{ °C};$<br>see <u>Figure 13</u>           | [1] - | 7.5  | 8.7       | mΩ  |
| R <sub>G</sub>                    | internal gate resistance (AC)     | f = 1 MHz   | -     | 1    | -         | Ω   |
| Dynamic o                         | characteristics                   |   |       |      |           |     |
| Q <sub>G(tot)</sub>               | total gate charge                 | $I_D = 0 A; V_{DS} = 0 V; V_{GS} = 10 V$  | -     | 44   | -         | nC  |
|                                   |                                   | $I_D = 25 \text{ A}; V_{DS} = 40 \text{ V}; V_{GS} = 10 \text{ V};$                                 | -     | 52   | -         | nC  |
| Q <sub>GS</sub>                   | gate-source charge                | see Figure 14; see Figure 15  | -     | 15   | -         | nC  |
| Q <sub>GS(th)</sub>               | pre-threshold gate-source charge  | $I_D = 25 \text{ A}; V_{DS} = 40 \text{ V}; V_{GS} = 10 \text{ V};$                                 | -     | 9.2  | -         | nC  |
| Q <sub>GS(th-pl)</sub>            | post-threshold gate-source charge | see Figure 14   | -     | 5.8  | -         | nC  |
| $Q_{GD}$                          | gate-drain charge                 | $I_D$ = 25 A; $V_{DS}$ = 40 V; $V_{GS}$ = 10 V;<br>see <u>Figure 14</u> ; see <u>Figure 15</u>      | -     | 11   | -         | nC  |
| $V_{GS(pl)}$                      | gate-source plateau voltage       | $I_D = 25 \text{ A}; V_{DS} = 40 \text{ V}; \text{ see } \frac{\text{Figure 15}}{\text{Figure 15}}$ | -     | 4.6  | -         | V   |
| C <sub>iss</sub>                  | input capacitance                 | $V_{DS} = 40 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$                                   | -     | 3346 | -         | рF  |
| C <sub>oss</sub>                  | output capacitance                | T <sub>j</sub> = 25 °C; see <u>Figure 16</u>  | -     | 296  | -         | рF  |
| C <sub>rss</sub>                  | reverse transfer capacitance      |   | -     | 158  | -         | рF  |
| t <sub>d(on)</sub>                | turn-on delay time                | $V_{DS}$ = 40 V; $R_L$ = 1.6 $\Omega$ ; $V_{GS}$ = 10 V;  | -     | 21   | -         | ns  |
| t <sub>r</sub>                    | rise time                         | $R_{G(ext)} = 4.7 \Omega$   | -     | 26   | -         | ns  |
| t <sub>d(off)</sub>               | turn-off delay time               |   | -     | 46   | -         | ns  |
| t <sub>f</sub>                    | fall time                         |   | -     | 20   | -         | ns  |
| Source-dra                        | ain diode                         |   |       |      |           |     |
| $V_{SD}$                          | source-drain voltage              | $I_S = 10 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C};$<br>see <u>Figure 17</u>      | -     | 0.79 | 1.2       | V   |

 Table 6.
 Characteristics ...continued

Tested to JEDEC standards where applicable.

| Symbol          | Parameter             | Conditions   | Min | Тур | Max | Unit |
|-----------------|-----------------------|--|-----|-----|-----|------|
| t <sub>rr</sub> | reverse recovery time | $I_S = 25 \text{ A}$ ; $dI_S/dt = 100 \text{ A/}\mu\text{s}$ ; | -   | 42  | -   | ns   |
| Q <sub>r</sub>  | recovered charge      | $V_{GS} = 0 \text{ V}; V_{DS} = 40 \text{ V}$                  | -   | 66  | -   | nC   |

[1] Measured 3 mm from package.

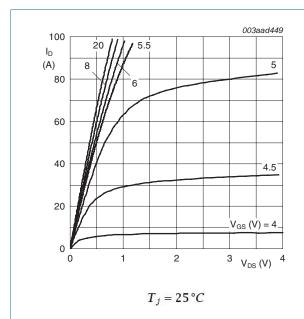


Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values

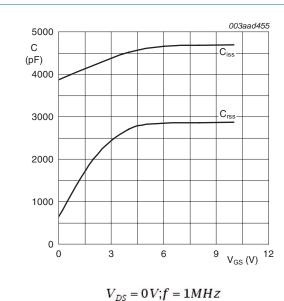


Fig 7. Input and reverse transfer capacitances as a function of gate-source voltage; typical values

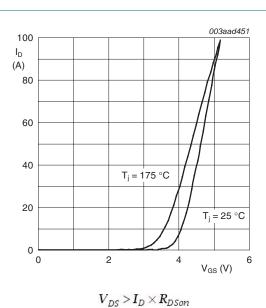
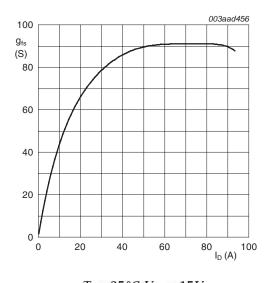


Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values



 $T_j = 25\,^{\circ}C; V_{DS} = 15\,V$ 

Fig 8. Forward transconductance as a function of drain current; typical values

PSMN8R7-80PS

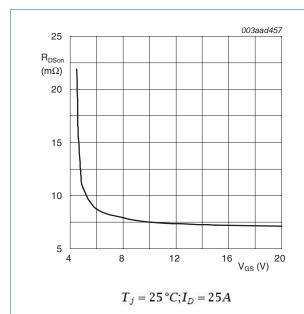


Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

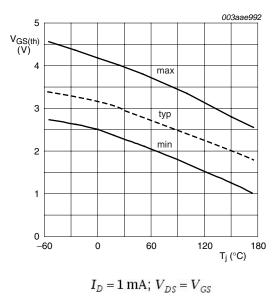


Fig 10. Gate-source threshold voltage as a function of junction temperature

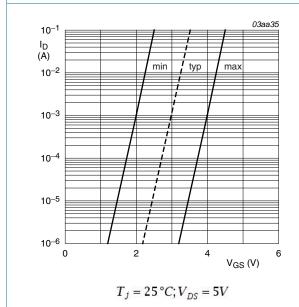


Fig 11. Sub-threshold drain current as a function of gate-source voltage

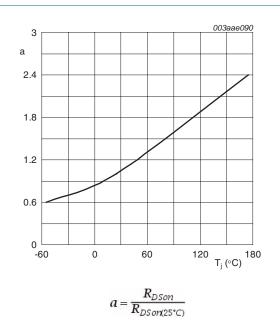


Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature

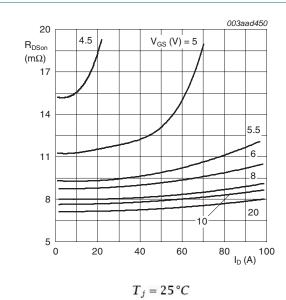


Fig 13. Drain-source on-state resistance as a function of drain current; typical values

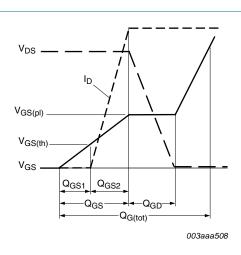


Fig 14. Gate charge waveform definitions

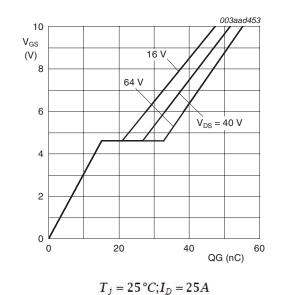
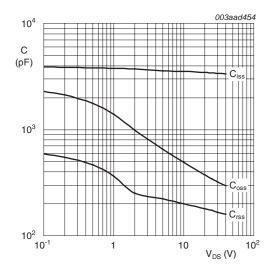


Fig 15. Gate-source voltage as a function of gate charge; typical values



 $V_{GS} = 0V; f = 1MHz$ 

Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

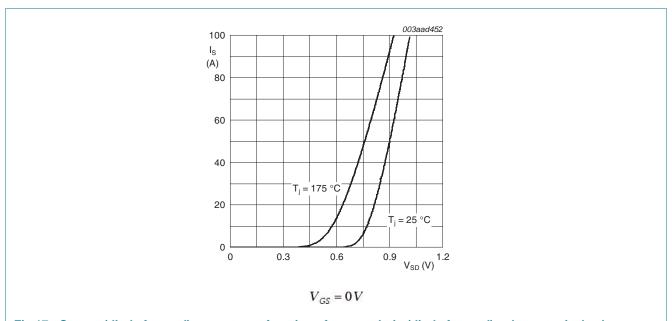


Fig 17. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

# Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB SOT78 mounting  $D_1$ base D L<sub>1</sub>(1)  $L_2^{(1)}$ Q  $(3\times)$ b<sub>2</sub>(2) (2×) 0 5 10 mm scale **DIMENSIONS** (mm are the original dimensions)

| UNI | T A          | A <sub>1</sub> | b          | b <sub>1</sub> (2) | b <sub>2</sub> (2) | С          | D            | D <sub>1</sub> | E           | е    | L            | L <sub>1</sub> (1) | L <sub>2</sub> <sup>(1)</sup><br>max. | р          | q          | Q          |  |
|-----|--------------|----------------|------------|--------------------|--------------------|------------|--------------|----------------|-------------|------|--------------|--------------------|---------------------------------------|------------|------------|------------|--|
| mn  | 1 4.7<br>4.1 | 1.40<br>1.25   | 0.9<br>0.6 | 1.6<br>1.0         | 1.3<br>1.0         | 0.7<br>0.4 | 16.0<br>15.2 | 6.6<br>5.9     | 10.3<br>9.7 | 2.54 | 15.0<br>12.8 | 3.30<br>2.79       | 3.0                                   | 3.8<br>3.5 | 3.0<br>2.7 | 2.6<br>2.2 |  |

- 1. Lead shoulder designs may vary.
- 2. Dimension includes excess dambar.

| OUTLINE |     | REFER           | ENCES | EUROPEAN | ISSUE DATE |                                 |
|---------|-----|-----------------|-------|----------|------------|---------------------------------|
| VERSION | IEC | JEDEC           | JEITA |          | PROJECTION | ISSUE DATE                      |
| SOT78   |     | 3-lead TO-220AB | SC-46 |          |            | <del>08-04-23</del><br>08-06-13 |

Fig 18. Package outline SOT78 (TO-220AB)

PSMN8R7-80PS

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# 8. Revision history

# Table 7. Revision history

| Document ID   | Release date                        | Data sheet status    | Change notice | Supersedes       |  |
|---|-------------------------------------|----------------------|---------------|------------------|--|
| PSMN8R7-80PS v.2  | 20101101                            | Product data sheet   | -             | PSMN8R7-80PS v.1 |  |
| Modifications:  • Status changed from objective to product. |                                     |                      |               |                  |  |
|   | <ul> <li>Various changes</li> </ul> | to content.          |               |                  |  |
| PSMN8R7-80PS v.1  | 20100129                            | Objective data sheet | -             | -                |  |

# 9. Legal information

### 9.1 Data sheet status

| Document status[1][2]          | Product status[3] | Definition  |
|--------------------------------|-------------------|---|
| Objective [short] data sheet   | Development       | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification     | This document contains data from the preliminary specification.                       |
| Product [short] data sheet     | Production        | This document contains the product specification.                                     |

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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# **PSMN8R7-80PS**

# N-channel 80 V 8.7 m $\Omega$ standard level MOSFET in TO-220

# 11. Contents

| 1   | Product profile          |
|-----|--------------------------|
| 1.1 | General description      |
| 1.2 | Features and benefits    |
| 1.3 | Applications             |
| 1.4 | Quick reference data1    |
| 2   | Pinning information      |
| 3   | Ordering information     |
| 4   | Limiting values3         |
| 5   | Thermal characteristics5 |
| 6   | Characteristics6         |
| 7   | Package outline          |
| 8   | Revision history12       |
| 9   | Legal information13      |
| 9.1 | Data sheet status        |
| 9.2 | Definitions13            |
| 9.3 | Disclaimers              |
| 9.4 | Trademarks14             |
| 10  | Contact information      |

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